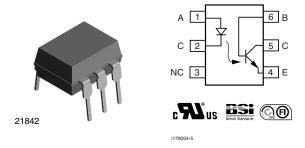
Vishay Semiconductors

Optocoupler, Phototransistor Output, with Base Connection



DESCRIPTION

The 4N25 family is an industry standard single channel phototransistor coupler. This family includes the 4N25, 4N26, 4N27, 4N28. Each optocoupler consists of gallium arsenide infrared LED and a silicon NPN phototransistor.

FEATURES

- Isolation test voltage 5000 V_{RMS}
- · Interfaces with common logic families
- Input-output coupling capacitance < 0.5 pF
- Industry standard dual-in-line 6 pin package
- Compliant to RoHS directive 2002/95/EC and in accordance to WEEE 2002/96/EC





APPLICATIONS

- AC mains detection
- · Reed relay driving
- Switch mode power supply feedback
- Telephone ring detection
- Logic ground isolation
- Logic coupling with high frequency noise rejection

AGENCY APPROVALS

- UL1577, file no. E52744
- BSI: EN 60065:2002, EN 60950:2000
- FIMKO: EN 60950, EN 60065, EN 60335

ORDER INFORMATION				
PART	REMARKS			
4N25	CTR > 20 %, DIP-6			
4N26	CTR > 20 %, DIP-6			
4N27	CTR > 10 %, DIP-6			
4N28	CTR > 10 %, DIP-6			

ABSOLUTE MAXIMUM RATINGS (1)							
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT			
INPUT		<u>.</u>					
Reverse voltage		V _R	5	V			
Forward current		I _F	60	mA			
Surge current	t ≤ 10 µs	I _{FSM}	3	Α			
Power dissipation		P _{diss}	100	mW			
ОUТРUТ							
Collector emitter breakdown voltage		V _{CEO}	70	V			
Emitter base breakdown voltage		V _{EBO}	7	V			
Collector current		Ic	50	mA			
Collector current	t≤1 ms	Ic	100	mA			
Power dissipation		P _{diss}	150	mW			



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ABSOLUTE MAXIMUM RATINGS (1)						
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT		
COUPLER						
Isolation test voltage		V _{ISO}	5000	V _{RMS}		
Creepage distance			≥ 7	mm		
Clearance distance			≥ 7	mm		
Isolation thickness between emitter and detector			≥ 0.4	mm		
Comparative tracking index	DIN IEC 112/VDE 0303, part 1		175			
In a latter and a late and	V _{IO} = 500 V, T _{amb} = 25 °C	R _{IO}	10 ¹²	Ω		
Isolation resistance	V _{IO} = 500 V, T _{amb} = 100 °C	R _{IO}	10 ¹¹	Ω		
Storage temperature		T _{stg}	- 55 to + 125	°C		
Operating temperature		T _{amb}	- 55 to + 100	°C		
Junction temperature		Tj	125	°C		
Soldering temperature (2)	max.10 s dip soldering: distance to seating plane ≥ 1.5 mm	T _{sld}	260	°C		

Notes

(1) T_{amb} = 25 °C, unless otherwise specified. Stresses in excess of the absolute maximum ratings can cause permanent damage to the device. Functional operation of the device is not implied at these or any other conditions in excess of those given in the operational sections of this document. Exposure to absolute maximum ratings for extended periods of the time can adversely affect reliability.

(2) Refer to reflow profile for soldering conditions for surface mounted devices (SMD). Refer to wave profile for soldering condditions for through hole devices (DIP).

PARAMETER	TEST COMPITION	PART	SYMBOL	MIN.	TVD	BAAV	LINUT
	TEST CONDITION	PARI	SYMBOL	WIIN.	TYP.	MAX.	UNIT
INPUT							
Forward voltage (2)	$I_F = 50 \text{ mA}$		V_{F}		1.3	1.5	V
Reverse current (2)	V _R = 3 V		I _R		0.1	100	μΑ
Capacitance	V _R = 0 V		Co		25		pF
OUTPUT							
Collector base breakdown voltage (2)	I _C = 100 μA		BV _{CBO}	70			V
Collector emitter breakdown voltage (2)	I _C = 1 mA		BV _{CEO}	30			V
Emitter collector breakdown voltage (2)	I _E = 100 μA		BV _{ECO}	7			V
	V _{CE} = 10 V, (base open)	4N25			5	50	nA
(dord) (2)		4N26			5	50	nA
I _{CEO} (dark) ⁽²⁾		4N27			5	50	nA
		4N28			10	100	nA
I _{CBO} (dark) (2)	V _{CB} = 10 V, (emitter open)				2	20	nA
Collector emitter capacitance	V _{CE} = 0		C _{CE}		6		pF
COUPLER			•				
Isolation test voltage (2)	Peak, 60 Hz		V _{IO}	5000			V
Saturation voltage, collector emitter	$I_{CE} = 2 \text{ mA}, I_{F} = 50 \text{ mA}$		V _{CE(sat)}			0.5	V
Resistance, input output (2)	V _{IO} = 500 V		R _{IO}	100			GΩ
Capacitance, input output	f = 1 MHz		C _{IO}		0.6		рF

Minimum and maximum values are testing requirements. Typical values are characteristics of the device and are the result of engineering evaluation. Typical values are for information only and are not part of the testing requirements.

(2) JEDEC registered values are 2500 V, 1500 V, 1500 V, and 500 V for the 4N25, 4N26, 4N27, and 4N28 respectively.



 $^{^{(1)}}$ $T_{amb} = 25$ °C, unless otherwise specified.

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CURRENT TRANSFER RATIO (1)							
PARAMETER	TEST CONDITION	PART	SYMBOL	MIN.	TYP.	MAX.	UNIT
DC current transfer ratio	V _{CE} = 10 V, I _F = 10 mA	4N25	CTR _{DC}	20	50		%
		4N26	CTR _{DC}	20	50		%
		4N27	CTR _{DC}	10	30		%
		4N28	CTR _{DC}	10	30		%

Note

⁽¹⁾ Indicates JEDEC registered values.

SWITCHING CHARACTERISTICS							
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT	
Rise and fall times	$V_{CE} = 10 \text{ V}, I_{F} = 10 \text{ mA}, R_{L} = 100 \Omega$	t _r , t _f		2		μs	

TYPICAL CHARACTERISTICS

T_{amb} = 25 °C, unless otherwise specified

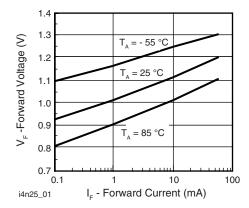


Fig. 1 - Forward Voltage vs. Forward Current

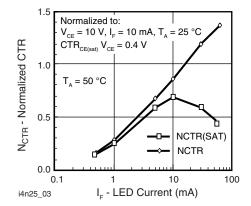


Fig. 3 - Normalized Non-Saturated and Saturated CTR vs. LED Current

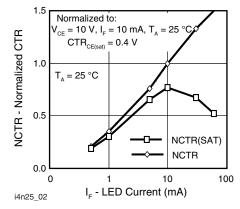


Fig. 2 - Normalized Non-Saturated and Saturated CTR vs. LED Current

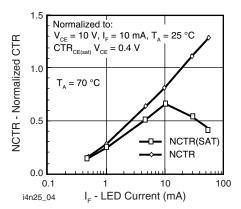


Fig. 4 - Normalized Non-Saturated and Saturated CTR vs. LED Current





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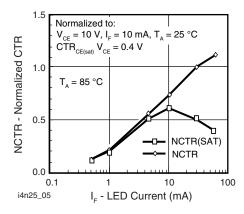


Fig. 5 - Normalized Non-Saturated and Saturated CTR vs. LED Current

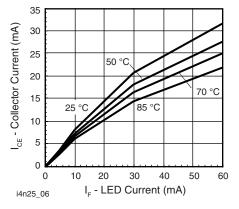


Fig. 6 - Collector Emitter Current vs. Temperature and LED Current

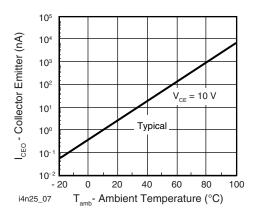


Fig. 7 - Collector Emitter Leakage Current vs. Temperature

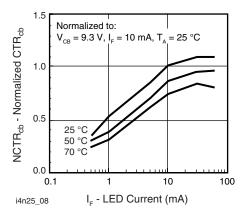


Fig. 8 - Normalized CTRcb vs. LED Current and Temperature

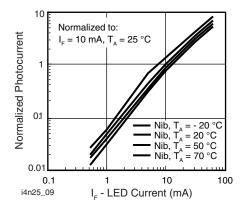


Fig. 9 - Normalized Photocurrent vs. I_{F} and Temperature

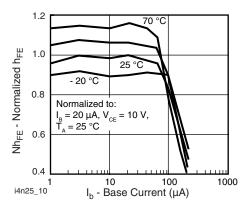


Fig. 10 - Normalized Non-Saturated h_{FE} vs. Base Current and Temperature



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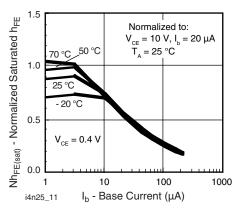


Fig. 11 - Normalized h_{FE} vs. Base Current and Temperature

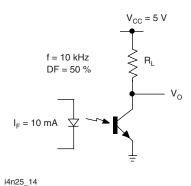


Fig. 14 - Switching Schematic

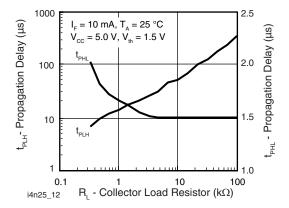


Fig. 12 - Propagation Delay vs. Collector Load Resistor

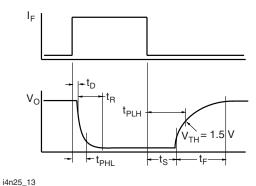


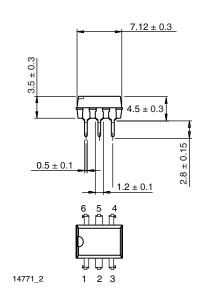
Fig. 13 - Switching Timing

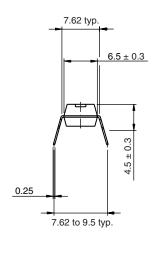




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PACKAGE DIMENSIONS in millimeters





PACKAGE MARKING



Legal Disclaimer Notice



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